

SANYO

No.3261A

2SB1232/2SD1842

2SB1232 : PNP Epitaxial Planar Silicon Transistor

2SD1842 : NPN Triple Diffused Planar Silicon Transistor

100V/40A Switching Applications**Features**

- Large current capacity and wide ASO.
- Low saturation voltage.

Applications

- Motor drivers, relay drivers, converters, and other general high-current switching applications

() : 2SB1232

Absolute Maximum Ratings at Ta = 25°C

			unit
Collector-to-Base Voltage	V_{CBO}	(-)110	V
Collector-to-Emitter Voltage	V_{CEO}	(-)100	V
Emitter-to-Base Voltage	V_{EBO}	(-)6	V
Collector Current	I_C	(-)40	A
Collector Current(Pulse)	I_{CP}	(-)65	A
Base Current	I_B	(-)12	A
Collector Dissipation	P_C	3.0	W
		150	W
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	- 55 to + 150	°C

 $T_c = 25^\circ\text{C}$ **Electrical Characteristics at Ta = 25°C**

			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = (-)100\text{V}, I_E = 0$			(-)0.1	mA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = (-)5\text{V}, I_C = 0$			(-)0.1	mA
DC Current Gain	$h_{FE(1)}$	$V_{CE} = (-)2\text{V}, I_C = (-)4\text{A}$	50※		140※	
	$h_{FE(2)}$	$V_{CE} = (-)2\text{V}, I_C = (-)16\text{A}$	20			
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = (-)16\text{A}, I_B = (-)1.6\text{A}$			(-)0.8	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = (-)16\text{A}, I_B = (-)1.6\text{A}$			(-)1.5	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = (-)1\text{mA}, I_E = 0$	(-)110			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = (-)5\text{mA}, R_{BE} = \infty$	(-)100			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = (-)1\text{mA}, I_C = 0$	(-)6			V

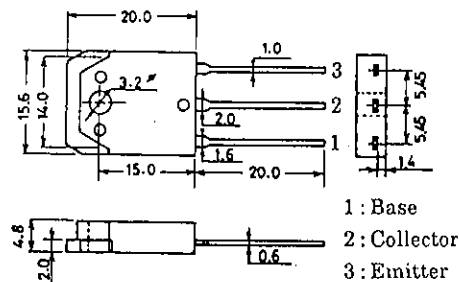
※ : For the $h_{FE(1)}$ of the 2SB1232/2SD1842, specify at least two ranks in principle.

50 P 100

70 Q 140

Package Dimensions 2022A

(unit : mm)



1 : Base

2 : Collector

3 : Emitter

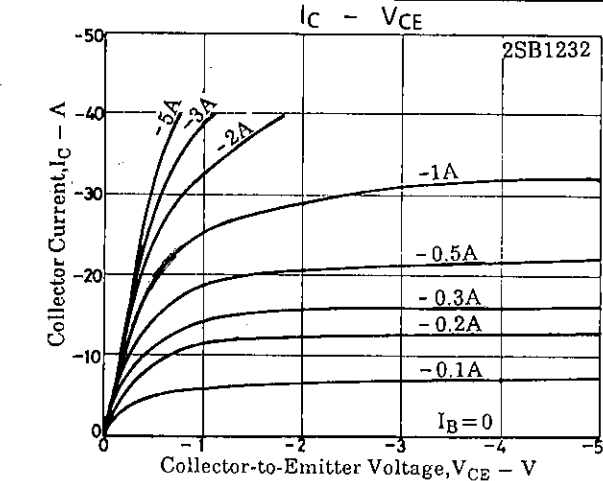
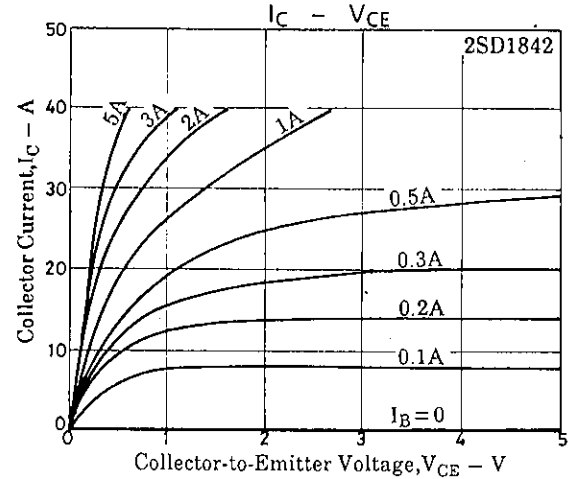
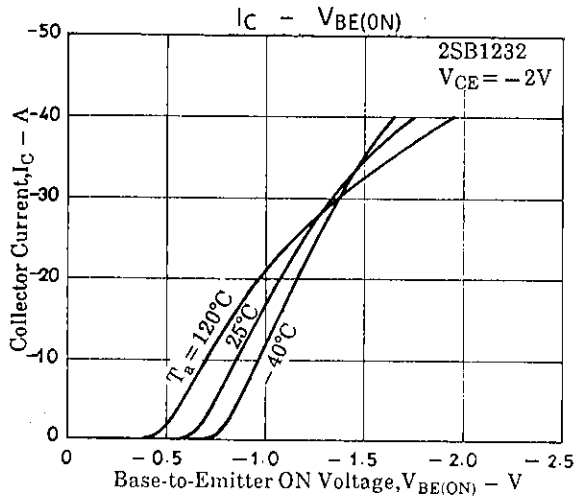
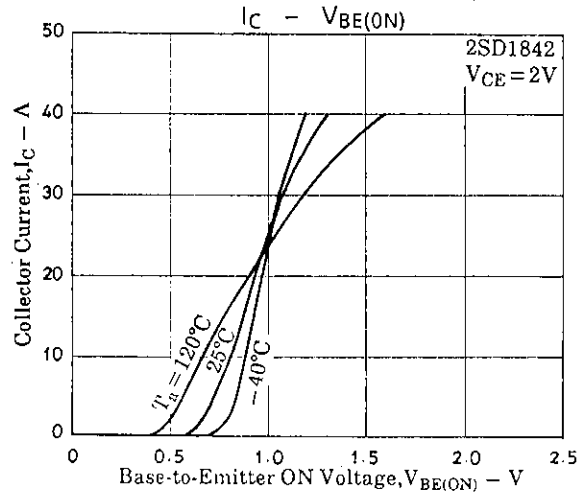
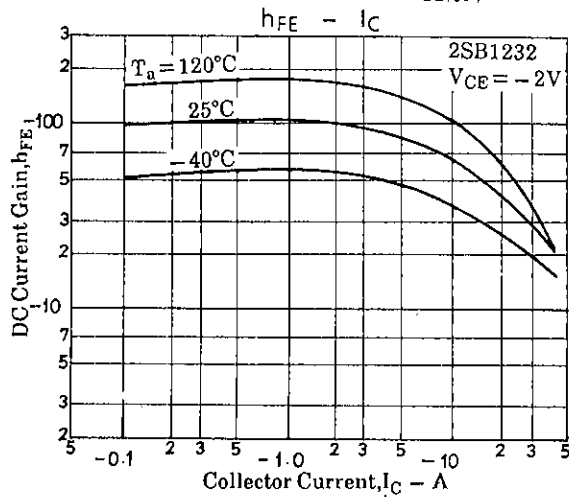
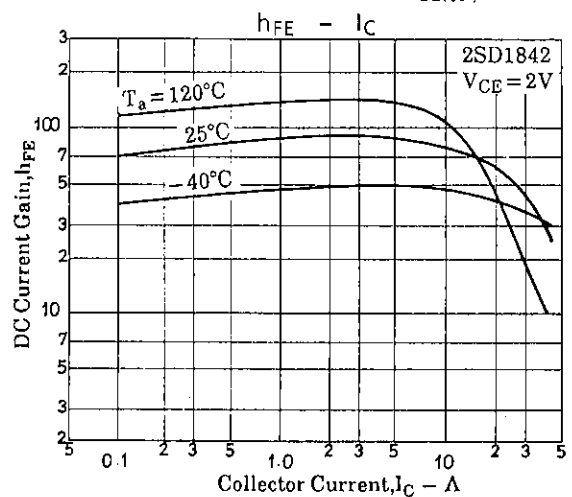
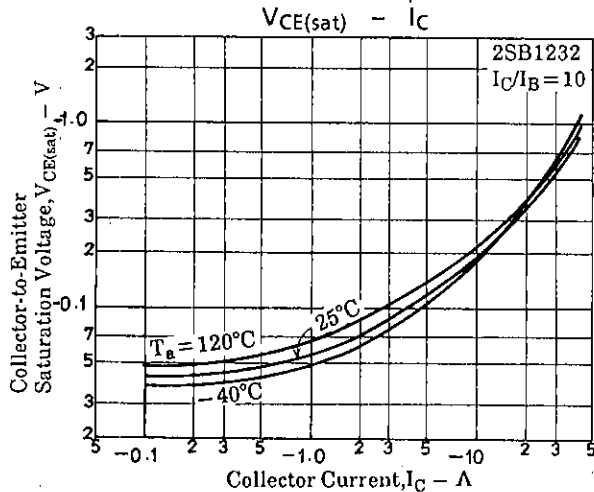
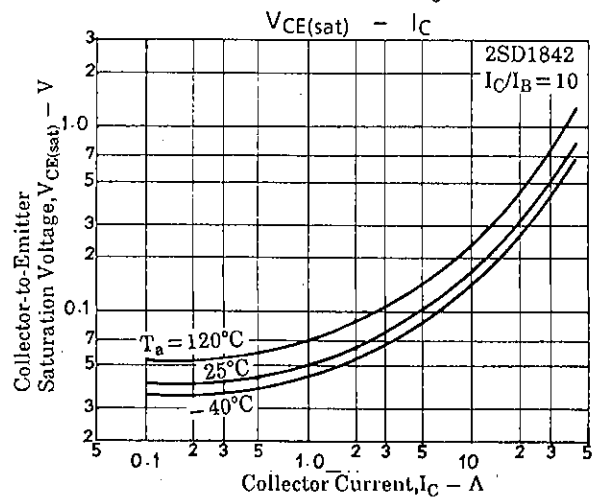
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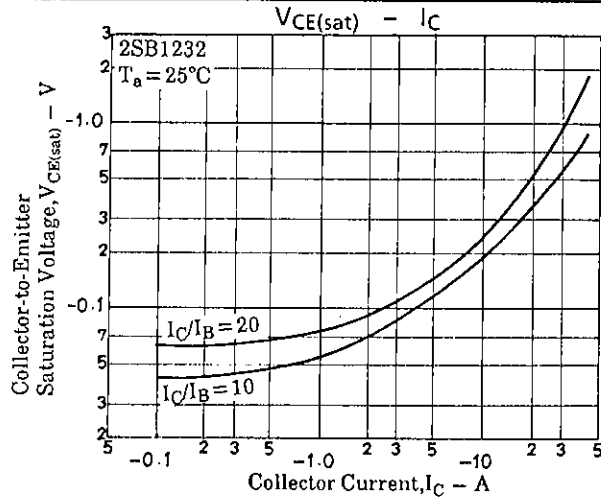
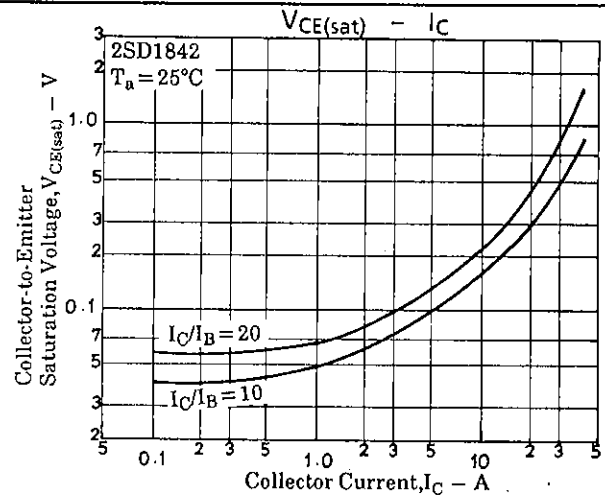
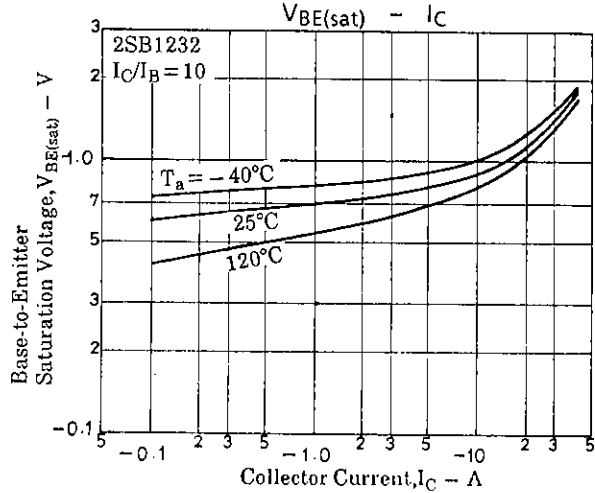
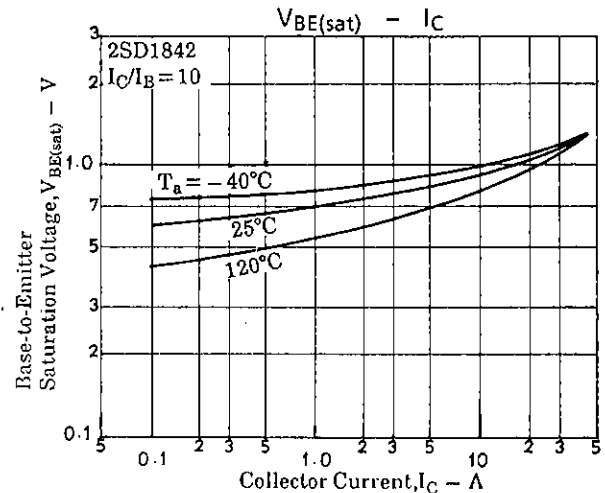
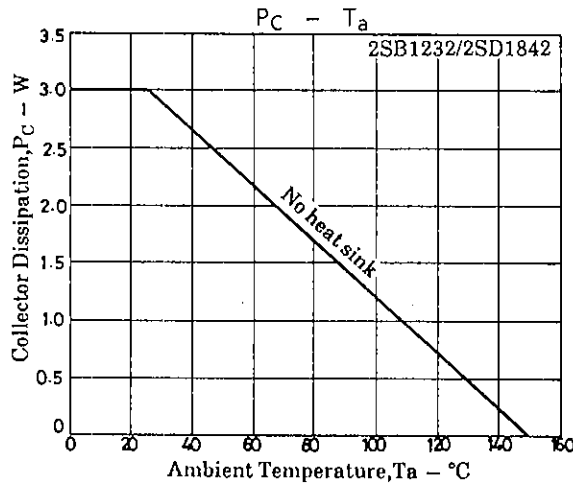
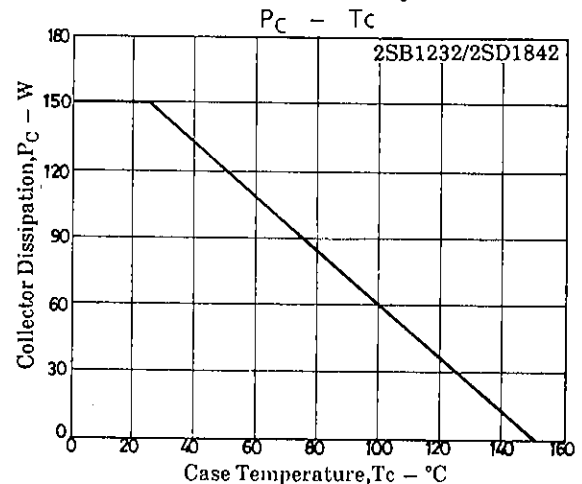
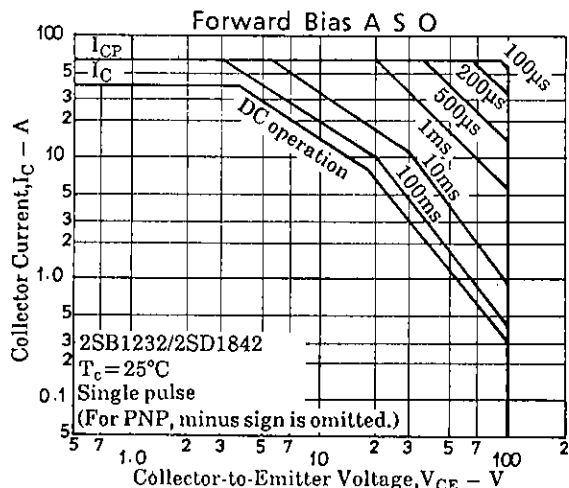
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110 JAPAN

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